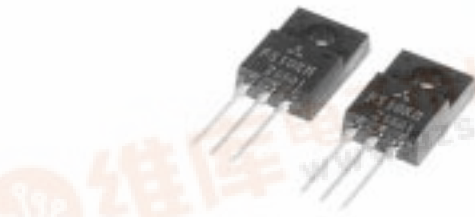


MITSUBISHI Nch POWER MOSFET

# FS10KM-2

HIGH-SPEED SWITCHING USE

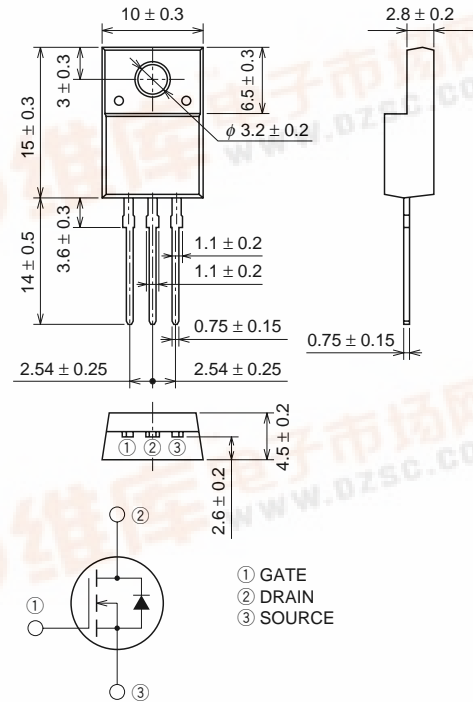
## FS10KM-2



- 10V DRIVE
- V<sub>DSS</sub> ..... 100V
- r<sub>DS (ON)</sub> (MAX) ..... 0.23Ω
- I<sub>D</sub> ..... 10A
- Integrated Fast Recovery Diode (TYP.) ..... 100ns
- V<sub>iso</sub> ..... 2000V

## OUTLINE DRAWING

Dimensions in mm



TO-220FN

## APPLICATION

Motor control, Lamp control, Solenoid control  
DC-DC converter, etc.

## MAXIMUM RATINGS (T<sub>c</sub> = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>DSS</sub>	Drain-source voltage	V <sub>GS</sub> = 0V	100	V
V <sub>GSS</sub>	Gate-source voltage	V <sub>DS</sub> = 0V	±20	V
I <sub>D</sub>	Drain current		10	A
I <sub>DM</sub>	Drain current (Pulsed)		40	A
I <sub>DA</sub>	Avalanche drain current (Pulsed)	L = 100μH	10	A
I <sub>S</sub>	Source current		10	A
I <sub>SM</sub>	Source current (Pulsed)		40	A
P <sub>D</sub>	Maximum power dissipation		20	W
T <sub>ch</sub>	Channel temperature		-55 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-55 ~ +150	°C
V <sub>iso</sub>	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g



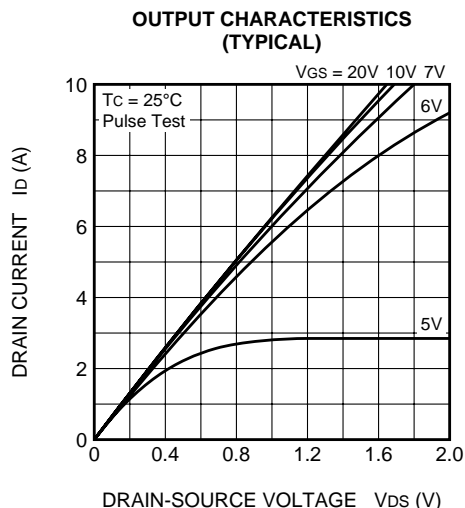
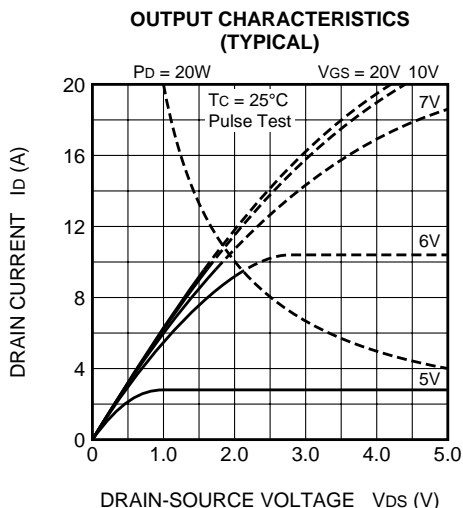
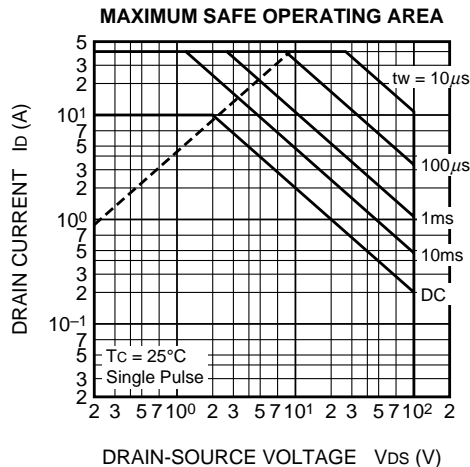
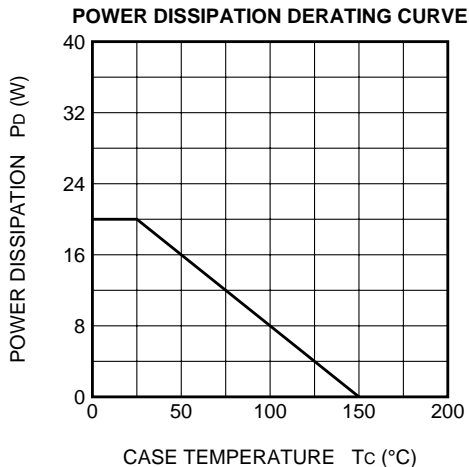
# FS10KM-2

## HIGH-SPEED SWITCHING USE

### ELECTRICAL CHARACTERISTICS (Tch = 25°C)

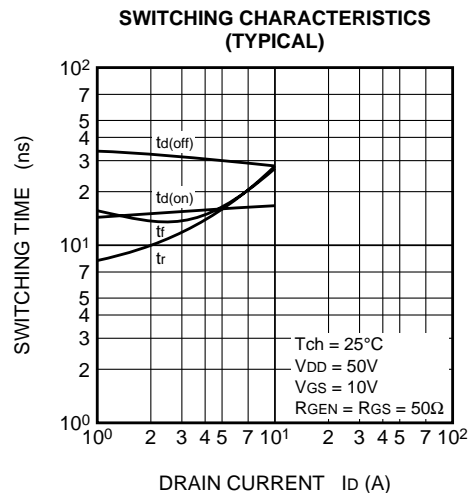
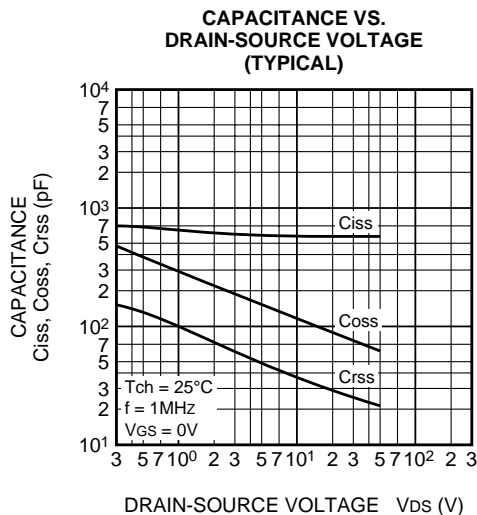
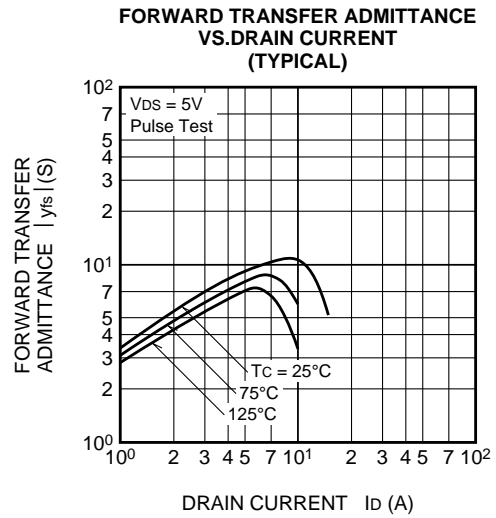
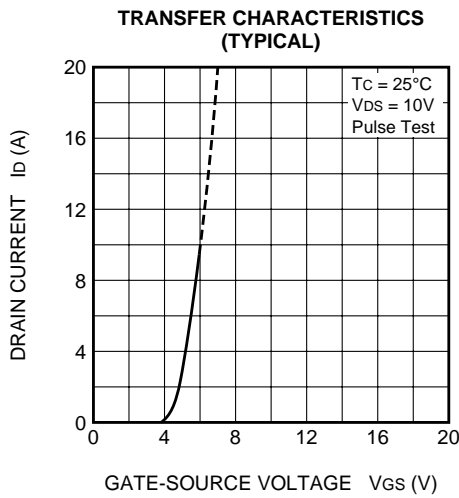
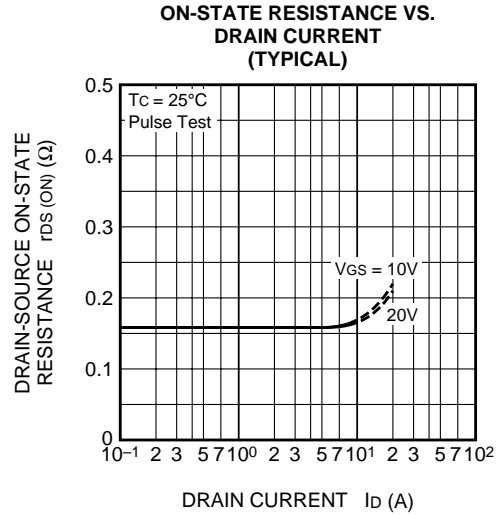
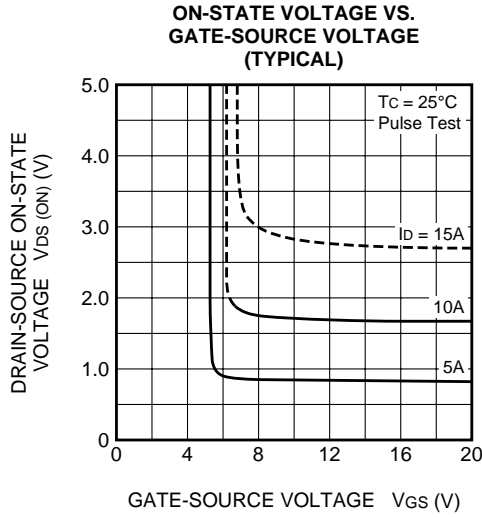
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	ID = 1mA, VGS = 0V	100	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	VDS = 100V, VGS = 0V	—	—	0.1	mA
VGS(th)	Gate-source threshold voltage	ID = 1mA, VDS = 10V	2.0	3.0	4.0	V
rDS(ON)	Drain-source on-state resistance	ID = 5A, VGS = 10V	—	0.16	0.23	Ω
VDS(ON)	Drain-source on-state voltage	ID = 5A, VGS = 10V	—	0.80	1.15	V
yfs	Forward transfer admittance	ID = 5A, VDS = 5V	—	9.0	—	S
Ciss	Input capacitance	Vbs = 10V, VGS = 0V, f = 1MHz	—	600	—	pF
Coss	Output capacitance		—	125	—	pF
Crss	Reverse transfer capacitance		—	40	—	pF
td(on)	Turn-on delay time	VDD = 50V, ID = 5A, VGS = 10V, RGEN = RGS = 50Ω	—	18	—	ns
tr	Rise time		—	20	—	ns
td(off)	Turn-off delay time		—	30	—	ns
tf	Fall time		—	18	—	ns
VSD	Source-drain voltage	IS = 5A, VGS = 0V	—	1.0	1.5	V
Rth(ch-c)	Thermal resistance	Channel to case	—	—	6.25	°C/W
trr	Reverse recovery time	IS = 10A, dis/dt = -100A/μs	—	100	—	ns

### PERFORMANCE CURVES



# FS10KM-2

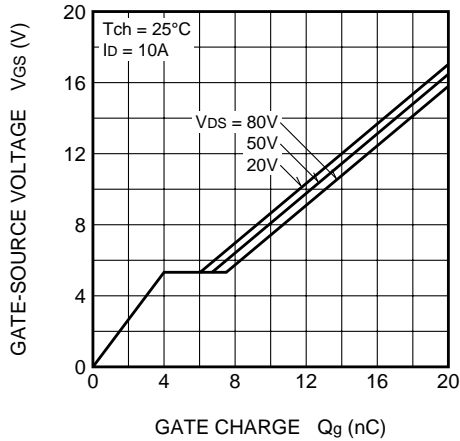
## HIGH-SPEED SWITCHING USE



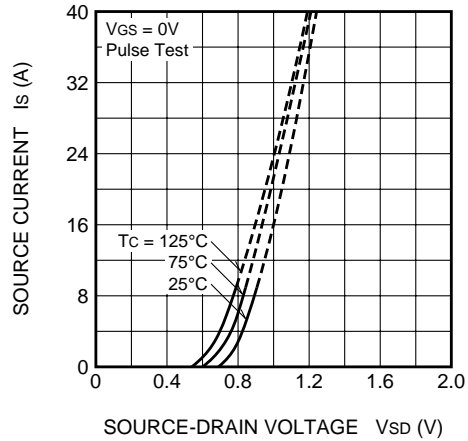
# FS10KM-2

HIGH-SPEED SWITCHING USE

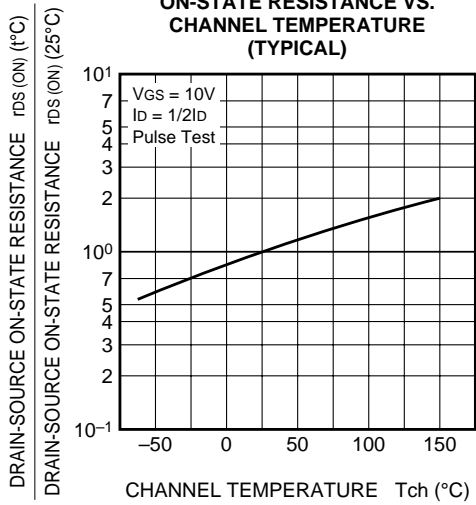
**GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)**



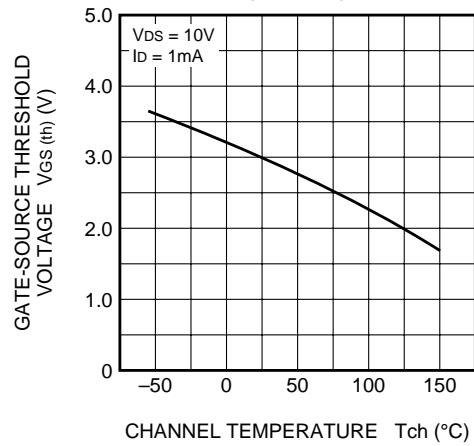
**SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)**



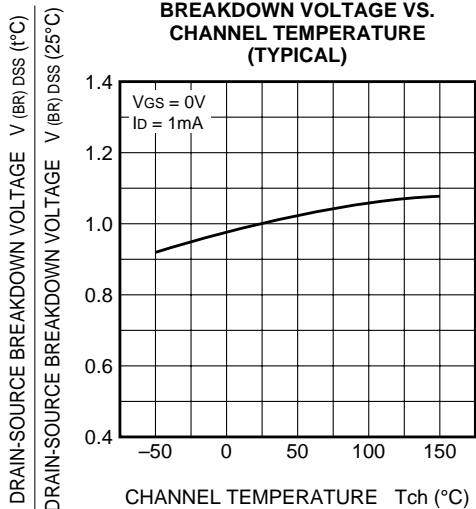
**ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)**



**THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)**



**BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS**

